TOSHIBA Intelligent Power Device Silicon Monolithic Power MOS IC

# **TPD1039S**

Low-Side Switch for Motor, Solenoid and Lamp Drive

TPD1039S is a monolithic power IC for low-side switch. The IC has a vertical MOSFET output which can be directly driven from a CMOS or TTL logic circuit (e.g., an MPU). The IC offers intelligent self-protection functions.

#### Features

- A monolithic power IC with a new structure combining a control block and a vertical power MOSFET ( $\pi$ -MOS) on a single chip.
- Can directly drive a power load from a CMOS or TTL logic.
- Built-in protection circuits against overvoltage, overheat, and overcurrent.
- Low ON-resistance:  $R_{DS}$  (ON) = 0.25  $\Omega$  (max) (@VIN = 5 V,  $T_{ch}$  = 25°C)
- Package TO-92 (MOD) can be packed in tape.

#### **Pin Assignment**

#### Marking



That because of its MOS structure, this product is sensitive to static electricity.



Weight: 0.36 g (typ.)

# **Block Diagram**



# **Pin Description**

Pin No.	Symbol	Pin Description
1	IN	Input pin. This pin is connected to a pull-down resistor internally, so that even when input wiring is open-circuited, output can never be turned on inadvertently.
2	DRAIN	Output pin. The current limit for output current is 5 A (typ.) when excessive current flow into a device because of in-rush current and short load of a lamp.
3	SOURCE	Ground pin.

# **Timing Chart**



### Truth Table

V <sub>IN</sub>	V <sub>DRAIN</sub>	State		
L	Н	Normal		
Н	L	Normai		
L	Н	Overcurrent		
Н	L	Overcurrent		
L	Н	Overtemporature		
Н	Н	Overtemperature		

### Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V <sub>DS (DC)</sub>	45	V
Drain current	I <sub>D (DC)</sub>	1.5	А
Input voltage	V <sub>IN</sub>	-0.5~6	V
Power dissipation (Ta = $25^{\circ}$ C)	PD	0.9	W
Single pulse active clamp capability (Note 1)	E <sub>AS</sub>	20	mJ
Active clamp current	I <sub>AR</sub>	1.5	А
Repetitive active clamp capability (Note 2)	E <sub>AR</sub>	0.09	mJ
Operating temperature	T <sub>opr</sub>	-40~85	°C
Channel temperature	T <sub>ch</sub>	150 (Note 3)	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C

Note 1: Active clamp capability (single pulse) test condition  $V_{DD}$  = 25 V, Starting T<sub>ch</sub> = 25°C, L = 10 mH, I<sub>AR</sub> = 1.5 A, R<sub>G</sub> = 25  $\Omega$ 

- Note 2: Repetitive rating; pulse width limited by maximum channel temperature.
- Note 3: Overtemperature protection will work when the channel temperature exceeds 125°C. Be sure to operate the device in such a way that the channel temperature does not exceed 125°C.
- Note4: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	R <sub>th (ch-a)</sub>	139	°C/W

### **Electrical Characteristics (T<sub>ch</sub> = 25°C)**

Characteristics	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Drain-source clamp voltage	V (CL) DSS	_	$V_{IN}=0~V,~I_D=1~mA$	45	_	_	V
High level input voltage	VIH	_	$V_{DS} = 1040 \text{ V}, \text{ I}_{D} \geqq 1 \text{ A}$	3.5	_	6	V
Low level input voltage	V <sub>IL</sub>	_	$V_{DS}$ = 10~40 V, $I_{D}$ $\leq$ 10 $\mu A$		_	0.8	V
Draint cut-off current	I <sub>DSS</sub>		$V_{IN}=0~V,~V_{DS}=40~V$			10	μA
Input current	I <sub>IN</sub>	_	$V_{IN} = 5 V$ , at normal operation	_	_	400	μA
Drain-source on resistance	R <sub>DS (ON)</sub>	_	$V_{IN} = 5 \ V, \ I_D = 1 \ A$	_	_	0.25	Ω
Thermal shutdown (Note 4)	Τ <sub>S</sub>	_	$V_{IN} = 5 V$	125	_	_	°C
Overcurrent protection	IS	_	$V_{IN} = 5 V$	_	5	_	А
Switching time	t <sub>ON</sub>	- 1		_	15	_	μs
	tOFF			_	45	_	
Source-drain diode forward voltage	V <sub>DSF</sub>		I <sub>F</sub> = 1.5 A	_	0.9	1.8	V

Note 4: Overtemperature protection will work when the channel temperature exceeds 125°C. Be sure to operate the device in such a way that the channel temperature does not exceed 125°C. The overtemperature protection function protects a device from destruction. Once started, however, this function will operate continuously; device reliability is not guaranteed while the function is in operation.

#### **Test Circuit 1**

#### Switching time measuring circuit

#### **Test circuit**

#### Measured waveforms













# Package Dimensions

SSIP3-P-1.27B



Weight: 0.36 g (typ.)

Unit : mm

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